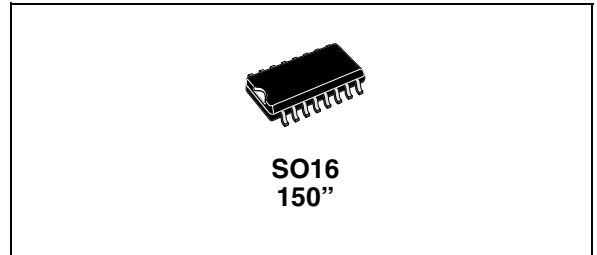


DiSEqC™ 2.1 Slave Microcontroller for LNBs and Switchers

The ST7LNB0 is an 8-bit microcontroller dedicated to DiSEqC™ slave operation in LNBs and switchers, it is compliant with the DiSEqC™ 2.1 level, also it supports backwards compatible (13/18 V, 22 kHz tone) and toneburst signalling.

- **Clock, Reset and Supply Management**
 - Reduced power consumption.
 - Safe power on/off management by low voltage detector (LVD).
 - Internal 8 MHz oscillator
- **Communication interface**
 - One DiSEqC™ 2.1 communication interface
- **Analog interface**
 - 13/18 V voltage detector
 - 22 KHz tone detector



- **I/O ports**
 - 8 output ports for control of committed and un-committed switches
 - 1 output port for standby control

Figure 1. ST7LNB0 Block Diagram

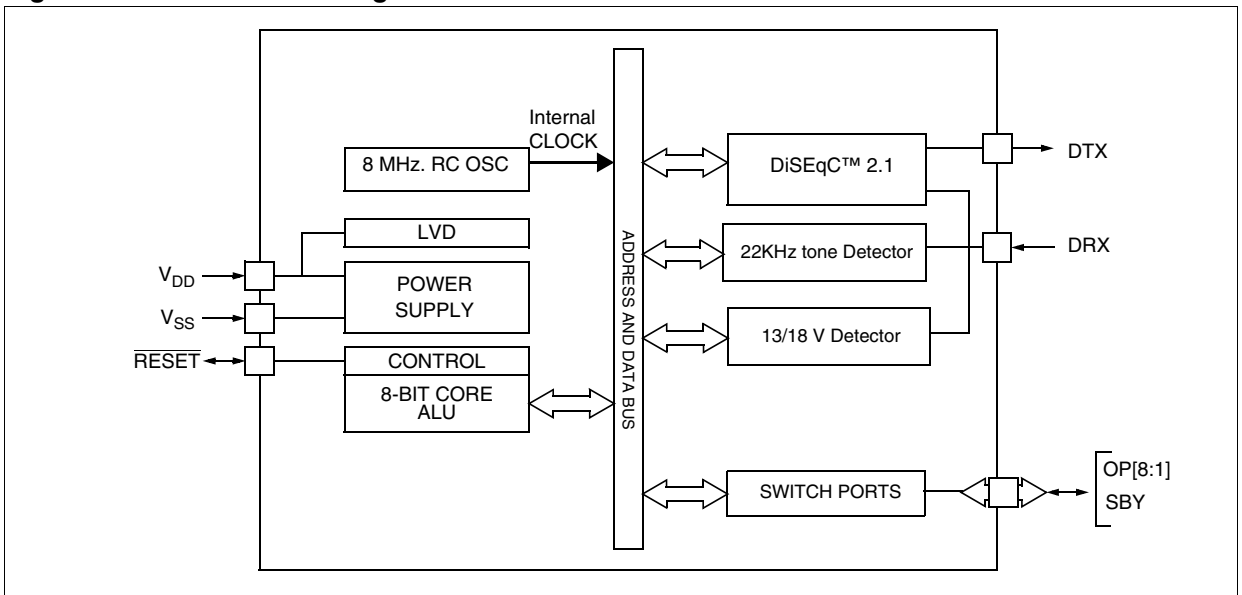
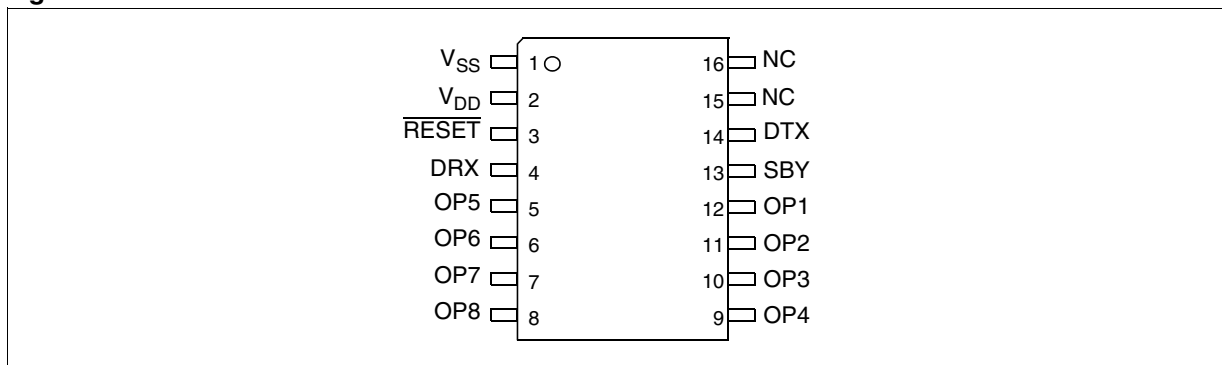


Table 1. Device Summary

Features	ST7LNB0Y0M6
Packages	SO16 150"
Peripherals	DiSEqC™ 2.1 communication interface, 22KHz tone detector, 13/18V detector
Operating Voltage	4.5 V to 5.5 V
Temperature range	-40°C to +85°C

1 ST7LNB0 PIN DESCRIPTION

Figure 2 ST7LNB0 Pinout



The following table gives the pin functions

Table 2. ST7LNB0 Pin Functions

Pin Number	Function Name	Function Description
1	V _{SS}	Ground
2	V _{DD}	Power Supply (+5 volts)
3	RESET	Reset (active low) input
4	DRX	Receive input
5	OP5	output 5 (uncommitted port)
6	OP6	output 6 (uncommitted port)
7	OP7	output 7 (uncommitted port)
8	OP8	output 8 (uncommitted port)
9	OP4	output 4 (SO B/A)
10 ¹⁾	OP3	output 3 (SB/SA)
11	OP2	output 2 (H/V)
12	OP1	output 1 (Hi/Lo)
13	SBY	STANDBY
14	DTX	DiSEqC™ data transmit output
15,16	-	Not used pins ²⁾

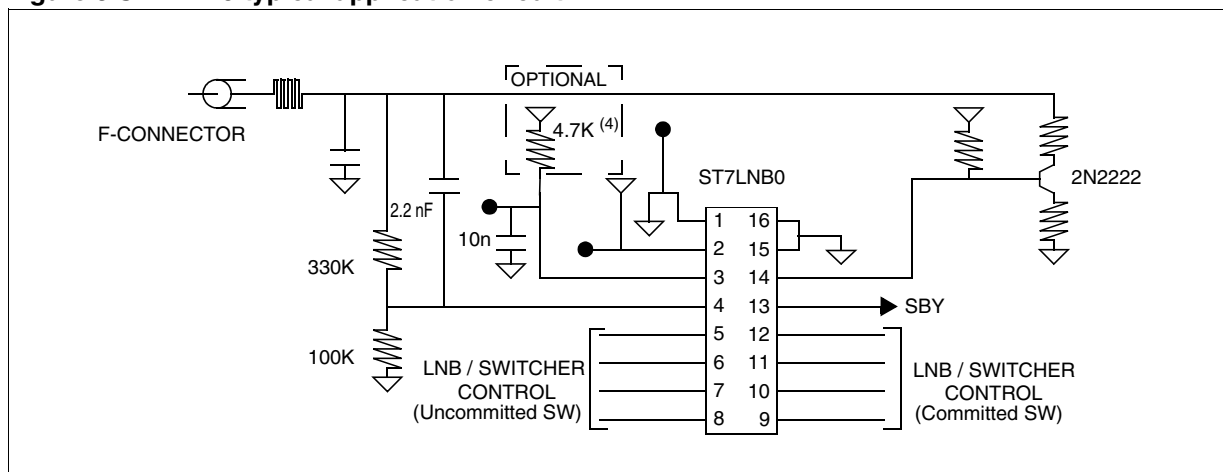
Notes:

1. During normal operation this pin must be pulled-up, internally or externally (external pull-up of 10k mandatory in noisy environment). This is to avoid entering ICC mode unexpectedly during a reset. In the application, even if the pin is configured as output, any reset will put it back in input pull-up
2. Unused pins 15 and 16 must be tied to ground.

2 ST7LNB0 IMPLEMENTATION

The following figure shows a typical application circuit for the ST7LNB0:

Figure 3 ST7LNB0 typical application circuit



Notes:

1. The divider chain connected to the DRX pin must have the following resistance values: 330K Ω and 100K Ω .
2. The reset circuitry linked to the RESET pin is optional, in fact the ST7LNB0 has an internal voltage level detector LVD which generates a static reset when the VDD supply is below a threshold voltage of 4.1 V.
3. The DiSEqC signalling must have a tone frequency of 22KHz(+/- 20%) and an amplitude exceeding 150 mV peak to peak.
4. When the LVD is enabled (default state), it is mandatory not to connect a pull-up resistor. A 10nF pull-down capacitor is recommended to filter noise on the reset line.

3 ST7LNB0 FUNCTIONAL DESCRIPTION

3.1 ST7LNB0 Configuration

Unlike the original slave microcontroller described in the “Eutelsat DiSEqC slave microcontroller version 1.0” the ST7LNB0 does not scan the control pins in order to determine the slave configuration, instead all configuration parameters must be programmed for each specific application, an Option List (Section 8) must be filled-in in order to program the necessary options at the manufacturing stage.

The slave configuration parameters are the following:

- The DiSEqC™ slave address e.g.: 11h for an LNB, 15h for a switcher.
- The Local oscillator frequency table entry numbers.
- The DiSEqC™ configuration byte (refer to DiSEqC slave microcontroller document page 15)
- The output mode (see next paragraph)
- 22 kHz tone use in backwards compatible mode (SB/SA or Hi/Lo switching)
- Standby pin use.

3.2 ST7LNB0 Switching Output Modes

The ST7LNB0 has 8 pins (OP1 to OP 8) available to provide ‘TTL’ logic levels to operate switches to select various signal conditions and sources (e.g. horizontal polarization, satellite position).

As listed in Table 2 the committed output port is composed of OP1 to OP4 and the uncommitted output port is composed of OP5 to OP8.

Depending on the application hardware, the switching control pins OP1 to OP8 may be operat-

ed differently. Three possible output modes can be configured:

Single polarity output mode. In this mode each pin can be controlled individually as described in the following table:

Table 3. Single polarity output mode

Pin Number	Function Name	Function Description
9	OP4	SO B/A
10	OP3	SB/SA
11	OP2	Hor/Ver
12	OP1	Hi/Lo
5	OP5	SW5
6	OP6	SW6
7	OP7	SW7
8	OP8	SW8

Decoded output mode. This mode offers the possibility to demultiplex three adjacent committed or uncommitted control lines (e.g Hi/Lo, SB/SA and SOB/A) in order to have a 1 of 8 demux on the output port OP1 to OP8. (for more details refer to DiSEqC™ slave microcontroller specification document page 10).

It is also possible to have a 1 of 4 demux by decoding only 2 control lines e.g. SB/SA and SO B/A for controlling a 1 of 4 switcher for example.

Complementary output mode. In this mode the state of the uncommitted switching output pins is the complementary of the state of the committed output ports pins (for more details refer to DiSEqC™ slave microcontroller document page 14).

4 SUPPORTED DiSEqC™ COMMANDS

Table 4. ST7LNB0 DiSEqC™ supported commands

Command number (Hex byte)	Command name	Command Function
00h	RESET	Reset DiSEqC™ microcontroller
01h	clr RESET	Clear the "RESET" flag
02h	STANDBY	Switch peripheral power off
03h	Power on	Switch peripheral power supply off
04h	Set Cont	Set contention flag
05h	Contend	Return address only if contention flag is set
06h	Clr Cont	Clear contention flag
07h	Address	Return address unless contention flag is set
08h	Move C	Change address only if contention flag is set
09h	Move	Change address unless contention flag is set
10h	STATUS	Read STATUS register
11h	Config	Read Configuration register
14h	Group 0	Read switching state (committed port)
15h	Group 1	Read switching state (uncommitted port)
20h	Set Lo	Select the low Local oscillator frequency
21h	Set VR	Select the vertical polarization
22h	Set Pos A	Select satellite position A
23h	Set SO A	Select switch Option A
24h	Set Hi	Select the Hi local oscillator frequency
25h	Set HL	Select the Horizontal polarization
26h	Set Pos B	Select satellite position B
27h	Set SO B	Select the switch Option B
28h	Set S1 A	Select switch S1 input A
29h	Set S2 A	Select switch S2 input A
2Ah	Set S3 A	Select switch S3 input A
2Bh	Set S4 A	Select switch S4 input A
2Ch	Set S1 B	Select switch S1 input B
2Dh	Set S2 B	Select switch S2 input B
2Eh	Set S3 B	Select switch S3 input B
2Fh	Set S4B	Select switch S4 input B
38h	Write N0	Write to port group 0 (committed switches)
39h	Write N1	Write to port group 1 (uncommitted switches)
51h	LO	Read current L.O frequency table entry number
52h	LO Lo	Read Lo L.O frequency table entry number
53h	LO Hi	Read Hi L.O frequency table entry number

Note:

After a power-on, the ST7LNB0 responds to backwards compatible signalling (13/18 V, 22 kHz, tone burst) until a valid DiSEqC frame is detected.

In order to return to backwards compatible mode, a RESET command must be sent.

5 ST7LNB0 CONFIGURATION

To configure the ST7LNB0 to the required target application, a dedicated DiSEqC command is implemented. This configuration is stored in the ST7LNB0 embedded EEPROM location.

5.1 COMMAND 0Fh

ST7LNB0 devices are shipped to customers with a default parameter value. These parameters can be updated using a dedicated 0Fh DiSEqC command.

This command has the following format where “data” is the parameter value to be programmed at the “index” location as shown in [Table 5](#).

E0h	DiSEqC Slave address	0Fh	index	data
-----	-------------------------	-----	-------	------

Note:

The special command E0 xx 0F FF FF protects the EEPROM data from any subsequent write access (where xx is the corresponding DiSEqC Slave address).

5.2 COMMAND 0Dh

For reading a parameter inside the EEPROM a dedicated 0Dh command has been added.

This command has the following format where “index” is the address in the EEPROM of the byte to be read (see [Table 5](#))

E2h	DiSEqC Slave address	0Dh	index
-----	-------------------------	-----	-------

:The reply frame has the following format where “data” is the read byte from the EEPROM:

E4h	data
-----	------

Timings:

the time required to update a byte parameter (write and read operation) is 130 ms
the time required to update all the parameters is about 3.5 s

Table 5. ST7LNB0 EEPROM Parameters

index	Parameter	Description	Default Value
00	slave address	DiSEqC slave address (00 to FFh), see note 1	14h
01	L.O frequencies	see note 2	00h
02	output configuration	see note 3	0Ah
03	Serial / version number	user can enter a value:0000h to FFFFh	1Bh, see note 4
04			FFh

Notes:

1. Besides the address defined in the EEPROM at index 00h, addresses 10h and 00h are recognized also as valid addresses.

2. L.O frequencies : Local oscillator table entry numbers.

- High nibble: High L.O frequency

- Low nibble: Low L.O frequency

3. Output configuration byte:

Bit Number	Bit Description	Value
0	22 KHz use	- 0: High/Low switching - 1: SB/SA switching
[1:4]	Decoded Mode Selection	- 0: mode not selected - [1 to 8] : decoded mode number
5	Complementary Mode Selection	- 0: mode not selected - 1: mode selected
6	2 Lines Decoded Mode Selection	- 0: mode not selected - 1: mode selected
7	Not Used	- 0

If neither the decoded mode nor the complementary mode is set then the "Single polarity mode" is selected by default.

4. Software version

6 ELECTRICAL CHARACTERISTICS

6.1 PARAMETER CONDITIONS

Unless otherwise specified, all voltages are referred to V_{SS} .

6.1.1 Minimum and Maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at $T_A=25^\circ\text{C}$ and $T_A=T_{A\text{max}}$ (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation ($\text{mean} \pm 3\Sigma$).

6.1.2 Typical values

Unless otherwise specified, typical data are based on $T_A=25^\circ\text{C}$, $V_{DD}=5\text{V}$ for the $4.5\text{V} \leq V_{DD} \leq 5.5\text{V}$ voltage range. They are given only as design guidelines and are not tested.

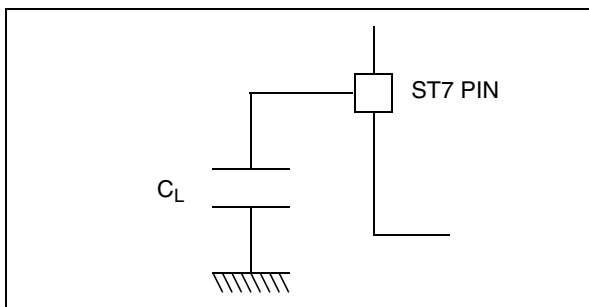
6.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in [Figure 4](#).

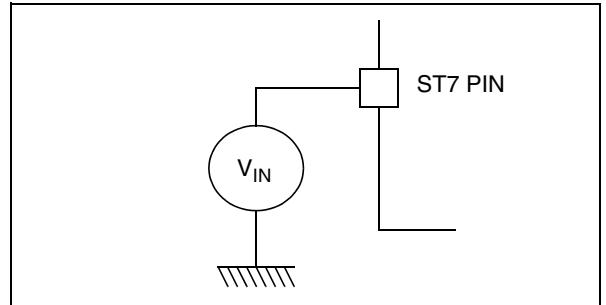
Figure 4. Pin loading conditions



6.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in [Figure 5](#).

Figure 5. Pin input voltage



6.2 ABSOLUTE MAXIMUM RATINGS

Stresses above those listed as “absolute maximum ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device under these condi-

tions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

6.2.1 Voltage Characteristics

Symbol	Ratings	Maximum value	Unit
$V_{DD} - V_{SS}$	Supply voltage	7.0	V
V_{IN}	Input voltage on any pin ^{1) & 2)}	$V_{SS}-0.3$ to $V_{DD}+0.3$	
$V_{ESD(HBM)}$	Electrostatic discharge voltage (Human Body Model)	see section 6.5.3 on page 13	
$V_{ESD(MM)}$	Electrostatic discharge voltage (Machine Model)		

6.2.2 Current Characteristics

Symbol	Ratings	Maximum value	Unit
I_{VDD}	Total current into V_{DD} power lines (source) ³⁾	100	mA
I_{VSS}	Total current out of V_{SS} ground lines (sink) ³⁾	100	
I_{IO}	Output current sunk by any standard I/O and control pin	25	
	Output current sunk by any high sink I/O pin	50	
	Output current source by any I/Os and control pin	- 25	
$I_{INJ(PIN)}$ ^{2) & 4)}	Injected current on \overline{RESET} pin	± 5	
	Injected current on any other pin ^{5) & 6)}	± 5	
$\Sigma I_{INJ(PIN)}$ ²⁾	Total injected current (sum of all I/O and control pins) ⁵⁾	± 20	

6.2.3 Thermal Characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	-65 to +150	°C
T_J	Maximum junction temperature (see Section 7.2 THERMAL CHARACTERISTICS)		

Notes:

1. Directly connecting the I/O pins to V_{DD} or V_{SS} could damage the device if an unexpected change of the I/O configuration occurs (for example, due to a corrupted program counter). To guarantee safe operation, this connection has to be done through a pull-up or pull-down resistor (typical: 10k Ω for I/Os). Unused I/O pins must be tied in the same way to V_{DD} or V_{SS} according to their reset configuration.
2. When the current limitation is not possible, the V_{IN} absolute maximum rating must be respected, otherwise refer to $I_{INJ(PIN)}$ specification. A positive injection is induced by $V_{IN} > V_{DD}$ while a negative injection is induced by $V_{IN} < V_{SS}$.
3. All power (V_{DD}) and ground (V_{SS}) lines must always be connected to the external supply.
4. Negative injection disturbs the analog performance of the device. In particular, it induces leakage currents throughout the device including the analog inputs. To avoid undesirable effects on the analog functions, care must be taken:
 - Analog input pins must have a negative injection less than 0.8 mA (assuming that the impedance of the analog voltage is lower than the specified limits)
 - Pure digital pins must have a negative injection less than 1.6mA. In addition, it is recommended to inject the current as far as possible from the analog input pins.
5. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values). These results are based on characterisation with $\Sigma I_{INJ(PIN)}$ maximum current injection on four I/O port pins of the device.
6. True open drain I/O port pins do not accept positive injection.

6.3 OPERATING CONDITIONS

6.3.1 General Operating Conditions:

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DD}	Supply voltage		4.5	5.5	V
T_A	Ambient temperature		-40	+85	°C

6.3.2 Operating Conditions with Low Voltage Detector (LVD)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{IT+(LVD)}$	Reset release threshold (V_{DD} rise)		4.00	4.25	4.50	V
$V_{IT-(LVD)}$	Reset generation threshold (V_{DD} fall)		3.80	4.10	4.30	
V_{hys}	LVD voltage threshold hysteresis	$V_{IT+(LVD)} - V_{IT-(LVD)}$		200		mV
V_{tPOR}	V_{DD} rise time rate ¹⁾		20		20000	$\mu\text{s/V}$
$t_{g(VDD)}$	Filtered glitch delay on V_{DD}	Not detected by the LVD			150	ns
$I_{DD(LVD)}$	LVD/AVD current consumption			200		μA

Notes:

1. Not tested in production. The V_{DD} rise time rate condition is needed to ensure a correct device power-on and LVD reset. When the V_{DD} slope is outside these values, the LVD may not ensure a proper reset of the MCU.

6.3.3 Operating Conditions with the DiSEqC™ Signalling

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{DiSEqC}	DiSEqC™ tone frequency		17.6	22	26.4	KHz
V_{DiSEqC}	DiSEqC™ tone voltage		150	650		mVpp
$V_{Backward}$	13/18 volt backward compatibility voltage threshold ¹⁾			15		V

Notes:

1. In backwards compatible mode, bus DC voltage is compared with 15 V, if it exceeds this voltage then it is considered as 13 V else it is considered as 18 V.

6.4 SUPPLY CURRENT CHARACTERISTICS

The following current consumption specified for the ST7 functional operating modes over temperature range does not take into account the clock

source current consumption. To get the total device consumption, the two current values must be added.

6.4.1 Supply Current

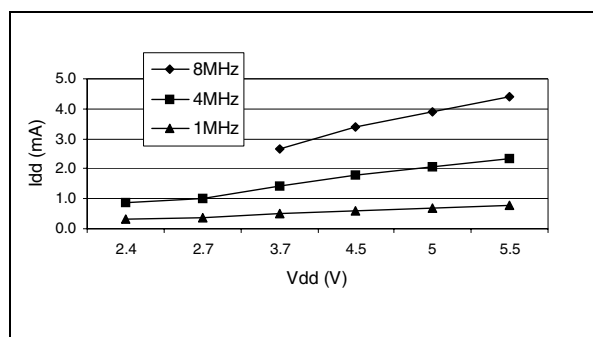
$T_A = -40$ to $+125^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Conditions	Typ	Max	Unit
I_{DD}	Supply current in RUN mode ¹⁾	$V_{DD}=5.5\text{V}$, $f_{CPU}=8\text{MHz}$	4.50	7	mA
	Supply current for LNB or switcher applications ²⁾			20	

Notes:

- CPU running with memory access, all I/O pins in input mode with a static value at V_{DD} or V_{SS} (no load), all peripherals in reset state; clock input (CLKIN) driven by external square wave, LVD disabled.
- Data based on typical ST7LNB0 LNB or switcher application software running.

Figure 6. Typical I_{DD} in RUN vs. f_{CPU}



6.5 EMC CHARACTERISTICS

Susceptibility tests are performed on a sample basis during product characterization.

6.5.1 Functional EMS (Electro Magnetic Susceptibility)

Based on a simple running application on the product (toggling 2 LEDs through I/O ports), the product is stressed by two electro magnetic events until a failure occurs (indicated by the LEDs).

- **ESD:** Electro-Static Discharge (positive and negative) is applied on all pins of the device until a functional disturbance occurs. This test conforms with the IEC 1000-4-2 standard.
- **FTB:** A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100pF capacitor, until a functional disturbance occurs. This test conforms with the IEC 1000-4-4 standard.

A device reset allows normal operations to be resumed. The test results are given in the table below based on the EMS levels and classes defined in application note AN1709.

6.5.1.1 Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical applica-

tion environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations:

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)

Prequalification trials:

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the RESET pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behaviour is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Symbol	Parameter	Conditions	Level/Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	$V_{DD}=5V$, $T_A=+25^{\circ}C$, $f_{OSC}=8MHz$ conforms to IEC 1000-4-2	2B
V_{FFTB}	Fast transient voltage burst limits to be applied through 100pF on V_{DD} and V_{DD} pins to induce a functional disturbance	$V_{DD}=5V$, $T_A=+25^{\circ}C$, $f_{OSC}=8MHz$ conforms to IEC 1000-4-4	3B

6.5.2 Electro Magnetic Interference (EMI)

Based on a simple application running on the product (toggling 2 LEDs through the I/O ports), the product is monitored in terms of emission. This emission test is in line with the norm SAE J 1752/3 which specifies the board and the loading of each pin.

Symbol	Parameter	Conditions	Monitored Frequency Band	Max vs. [f_{OSC}/f_{CPU}]		Unit
				1/4MHz	1/8MHz	
S_{EMI}	Peak level	$V_{DD}=5V$, $T_A=+25^{\circ}C$, SO16 package, conforming to SAE J 1752/3	0.1MHz to 30MHz	8	14	dB μ V
			30MHz to 130MHz	27	32	
			130MHz to 1GHz	26	28	
			SAE EMI Level	3.5	4	-

Notes:

1. Data based on characterization results, not tested in production.

EMC CHARACTERISTICS (Cont'd)

6.5.3 Absolute Maximum Ratings (Electrical Sensitivity)

Based on three different tests (ESD, LU and DLU) using specific measurement methods, the product is stressed in order to determine its performance in terms of electrical sensitivity. For more details, refer to the application note AN1181.

6.5.3.1 Electro-Static Discharge (ESD)

Electro-Static Discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts*(n+1) supply pin). This test conforms to the JESD22-A114A/A115A standard.

Absolute Maximum Ratings

Symbol	Ratings	Conditions	Maximum value ¹⁾	Unit
$V_{ESD(HBM)}$	Electro-static discharge voltage (Human Body Model)	$T_A=+25^{\circ}\text{C}$	4000	V

Notes:

1. Data based on characterization results, not tested in production.

6.5.3.2 Static and Dynamic Latch-Up

■ **LU:** 3 complementary static tests are required on 10 parts to assess the latch-up performance. A supply overvoltage (applied to each power supply pin) and a current injection (applied to each input, output and configurable I/O pin) are performed on each sample. This test conforms to the EIA/JESD 78 IC latch-up standard. For more details, refer to the application note AN1181.

■ **DLU:** Electro-Static Discharges (one positive then one negative test) are applied to each pin of 3 samples when the micro is running to assess the latch-up performance in dynamic mode. Power supplies are set to the typical values, the oscillator is connected as near as possible to the pins of the micro and the component is put in reset mode. This test conforms to the IEC1000-4-2 and SAEJ1752/3 standards. For more details, refer to the application note AN1181.

Electrical Sensitivities

Symbol	Parameter	Conditions	Class ¹⁾
LU	Static latch-up class	$T_A=+25^{\circ}\text{C}$	A
DLU	Dynamic latch-up class	$V_{DD}=5.5\text{V}$, $f_{OSC}=4\text{MHz}$, $T_A=+25^{\circ}\text{C}$	A

Notes:

1. Class description: A Class is an STMicroelectronics internal specification. All its limits are higher than the JEDEC specifications, that means when a device belongs to Class A it exceeds the JEDEC standard. B Class strictly covers all the JEDEC criteria (international standard).

6.6 I/O PORT PIN CHARACTERISTICS

6.6.1 General Characteristics

Subject to general operating conditions for V_{DD} , f_{OSC} , and T_A unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IL}	Input low level voltage				$0.3 \times V_{DD}$	V
V_{IH}	Input high level voltage		$0.7 \times V_{DD}$			
V_{hys}	Schmitt trigger voltage hysteresis ¹⁾			400		mV
I_L	Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$			± 1	μA
I_S	Static current consumption ²⁾	Floating input mode			200	
R_{PU}	Weak pull-up equivalent resistor ³⁾	$V_{IN} = V_{SS}, V_{DD} = 5V$	50	120	250	$k\Omega$
C_{IO}	I/O pin capacitance			5		pF
$t_{f(I/O)out}$	Output high to low level fall time ¹⁾	$C_L = 50pF$ Between 10% and 90%		25		ns
$t_{r(I/O)out}$	Output low to high level rise time ¹⁾			25		

Notes:

1. Data based on characterization results, not tested in production.
2. Configuration not recommended, all unused pins must be kept at a fixed voltage: using the output mode of the I/O for example or an external pull-up or pull-down resistor (see Figure 7). Data based on design simulation and/or technology characteristics, not tested in production.
3. The R_{PU} pull-up equivalent resistor is based on a resistive transistor (corresponding I_{PU} current characteristics described in Figure 8).

Figure 7. Two typical Applications with unused I/O Pin

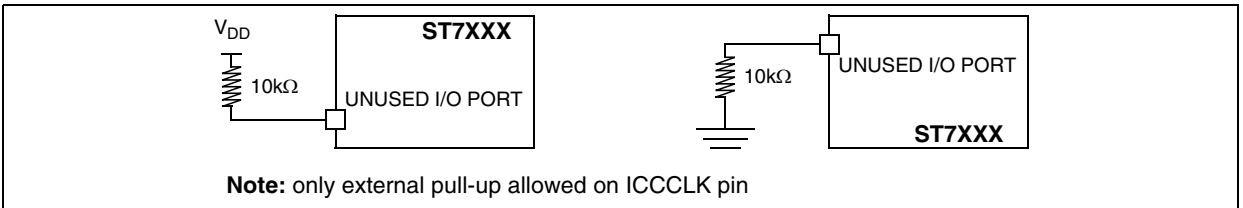
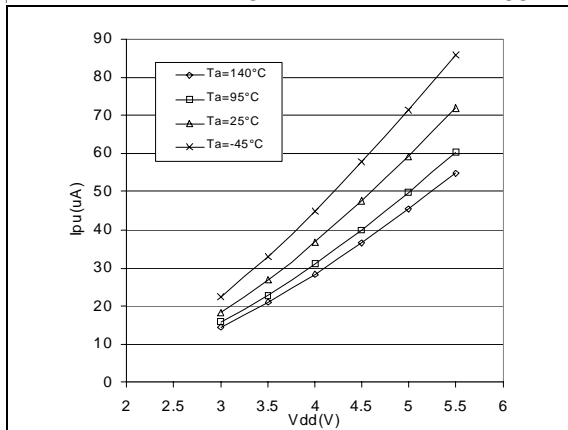


Figure 8. Typical I_{PU} vs. V_{DD} with $V_{IN} = V_{SS}$



I/O PORT PIN CHARACTERISTICS (Cont'd)

6.6.2 Output Driving Current

Subject to general operating conditions for V_{DD} , f_{CPU} , and T_A unless otherwise specified.

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{OL}^{1)}$	Output low level voltage for a standard I/O pin when 8 pins are sunk at same time (see Figure 9)	$I_{IO}=+5mA$		1.0	V
		$I_{IO}=+2mA$		0.4	
		$I_{IO}=+20mA$		1.3	
		$I_{IO}=+8mA$		0.75	
$V_{OH}^{2)}$	Output high level voltage for an I/O pin when 4 pins are sourced at same time (see Figure 11)	$I_{IO}=-5mA$	$V_{DD}-1.5$		
		$I_{IO}=-2mA$	$V_{DD}-0.8$		

Notes:

1. The I_{IO} current sunk must always respect the absolute maximum rating specified in Section 6.2.2 and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VSS} .
2. The I_{IO} current sourced must always respect the absolute maximum rating specified in Section 6.2.2 and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VDD} . True open drain I/O pins does not have V_{OH} .
3. Not tested in production, based on characterization results.

Figure 9. Typical V_{OL} at $V_{DD}=5V$ (standard)

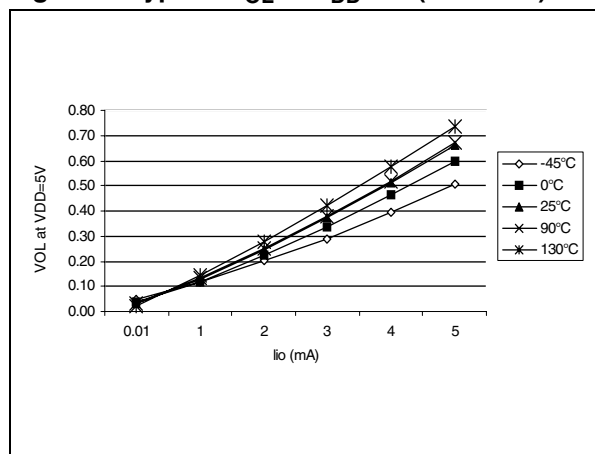


Figure 10. Typical V_{OL} at $V_{DD}=5V$ (high-sink)

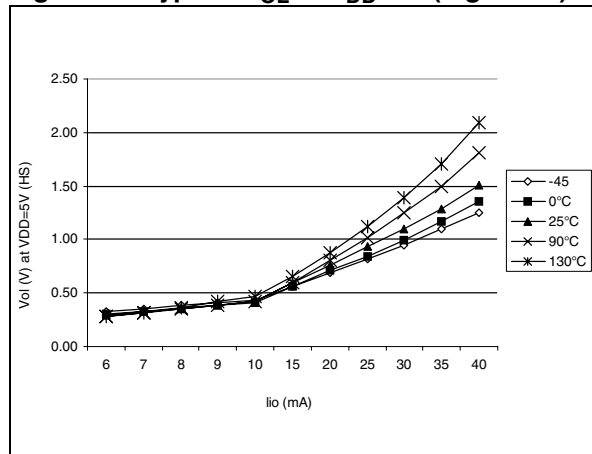
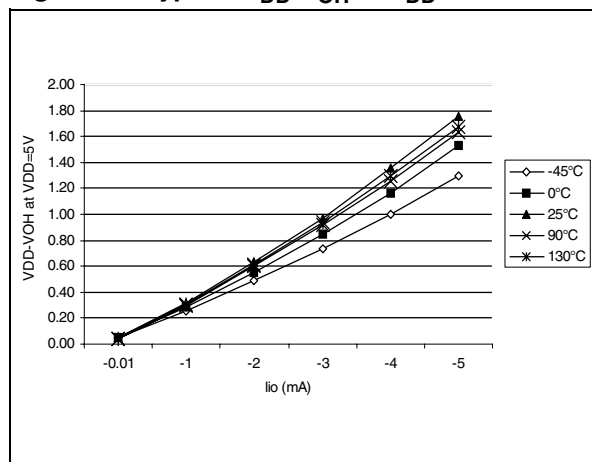


Figure 11. Typical $V_{DD}-V_{OH}$ at $V_{DD}=5V$



6.7 CONTROL PIN CHARACTERISTICS

6.7.1 Asynchronous $\overline{\text{RESET}}$ Pin

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IL}	Input low level voltage				$0.3 \times V_{DD}$	V
V_{IH}	Input high level voltage		$0.7 \times V_{DD}$			
V_{hys}	Schmitt trigger voltage hysteresis ¹⁾			1		V
V_{OL}	Output low level voltage ²⁾	$V_{DD}=5V$	$I_{IO}=+5mA$	0.5	1.0	V
			$I_{IO}=+2mA$	0.2	0.4	
R_{ON}	Pull-up equivalent resistor ^{3) 1)}	$V_{DD}=5V$	20	40	80	k Ω
$t_{w(RSTL)out}$	Generated reset pulse duration	Internal reset sources		30		μs
$t_{h(RSTL)in}$	External reset pulse hold time ⁴⁾		20			μs
$t_{g(RSTL)in}$	Filtered glitch duration ⁵⁾			200		ns

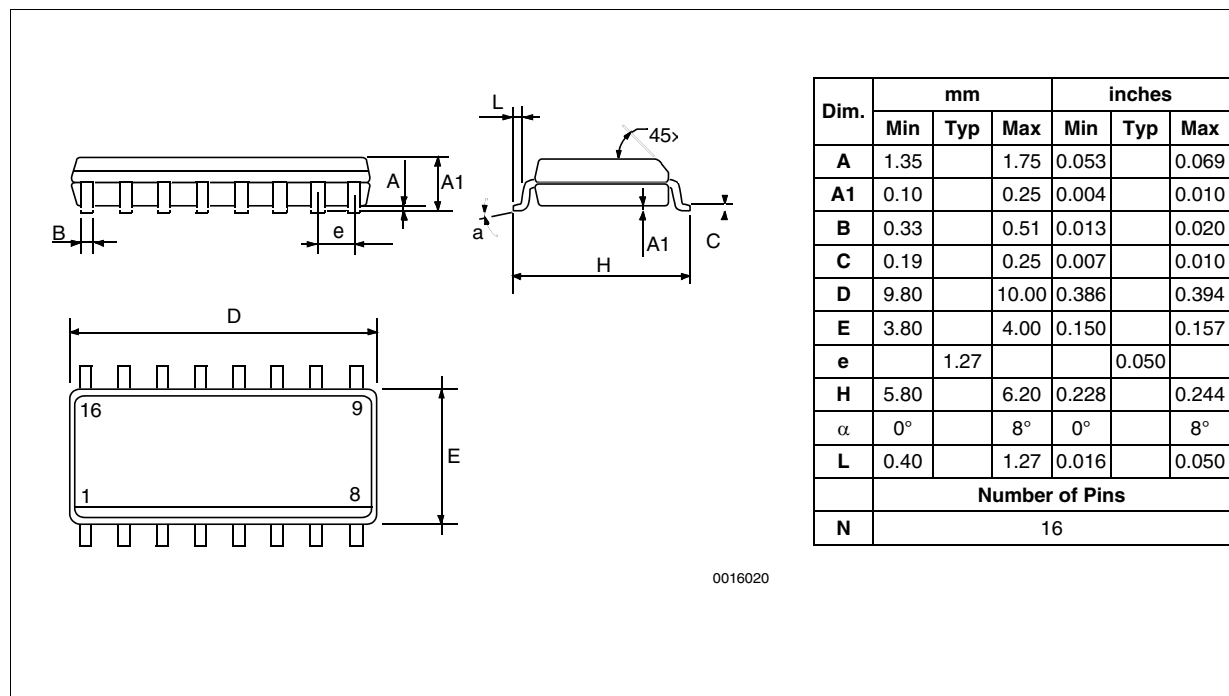
Notes:

1. Data based on characterization results, not tested in production.
2. The I_{IO} current sunk must always respect the absolute maximum rating specified in [Section 6.2.2](#) and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VSS} .
3. The R_{ON} pull-up equivalent resistor is based on a resistive transistor. Specified for voltage on $\overline{\text{RESET}}$ pin between V_{ILmax} and V_{DD} .
4. To guarantee the reset of the device, a minimum pulse has to be applied to the $\overline{\text{RESET}}$ pin. All short pulses applied on $\overline{\text{RESET}}$ pin with a duration below $t_{h(RSTL)in}$ can be ignored.
5. The reset network protects the device against parasitic resets.
6. The output of the external reset circuit must have an open-drain output to drive the ST7 reset pad. Otherwise the device can be damaged when the ST7 generates an internal reset (LVD or watchdog).
7. Whatever the reset source is (internal or external), the user must ensure that the level on the $\overline{\text{RESET}}$ pin can go below the V_{IL} max. level specified in section 6.7.1 on page 16. Otherwise the reset will not be taken into account internally.
8. Because the reset circuit is designed to allow the internal $\overline{\text{RESET}}$ to be output in the $\overline{\text{RESET}}$ pin, the user must ensure that the current sunk on the $\overline{\text{RESET}}$ pin (by an external pull-up for example) is less than the absolute maximum value specified for $I_{INJ(\overline{\text{RESET}})}$ in section 6.2.2 on page 9.

7 PACKAGE CHARACTERISTICS

7.1 PACKAGE MECHANICAL DATA

Figure 12. 16-Pin Plastic Small Outline Package, 150-mil Width



7.2 THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R_{thJA}	Package thermal resistance (junction to ambient)	TBD	°C/W
P_D	Power dissipation ¹⁾	500	mW
T_{Jmax}	Maximum junction temperature ²⁾	150	°C

Notes:

1. The power dissipation is obtained from the formula $P_D = P_{INT} + P_{PORT}$ where P_{INT} is the chip internal power ($I_{DD} \times V_{DD}$) and P_{PORT} is the port power dissipation determined by the user.

2. The average chip-junction temperature can be obtained from the formula $T_J = T_A + P_D \times R_{thJA}$.

7.3 SOLDERING AND GLUEABILITY INFORMATION

Recommended soldering information given only as design guidelines.

Figure 13. Recommended Wave Soldering Profile (with 37% Sn and 63% Pb)

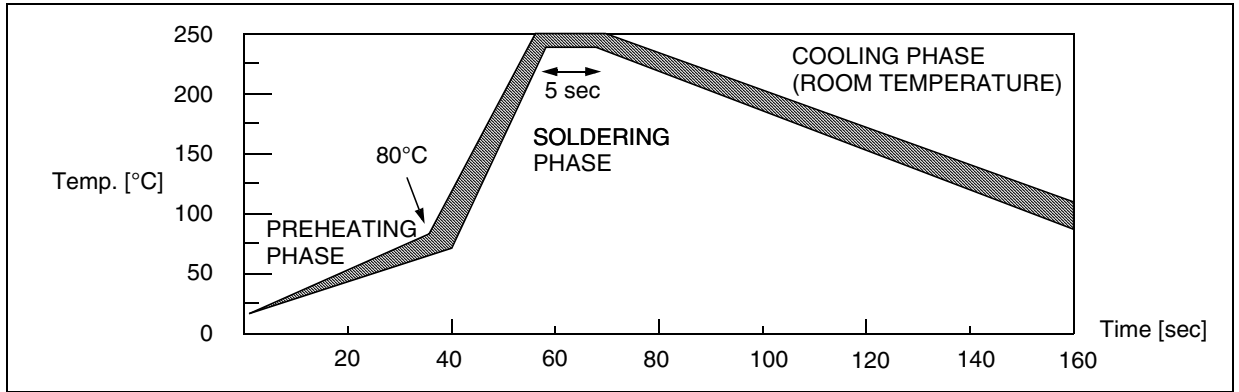
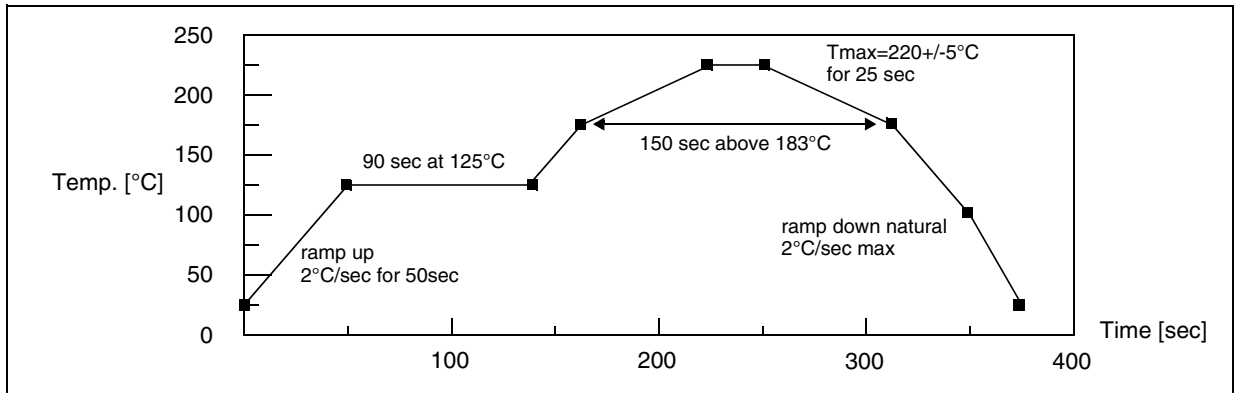


Figure 14. Recommended Reflow Soldering Oven Profile (MID JEDEC)



Recommended glue for SMD plastic packages:

- Heraeus: PD945, PD955
- Loctite: 3615, 3298

8 DEVICE CONFIGURATION

8.1 DATA EEPROM OPTION BYTES

Byte Name	Description	Address
FAM	Device Family Address (11h:LNB ; 15h: switcher)	1002h
LOFREQ	Local Oscillator Frequency Table Entry Numbers	1003h
PARAM	Output Mode and 22 kHz Tone Use (Hi/Lo or SB/SA)	1004h

FAM OPTION BYTE

Device Family Address.

11h: Normal LNB

15h: Normal Switcher

LOFREQ OPTION BYTE

Local Oscillator Frequency Table Entry Number

This byte indicates the value of a LNB local oscillator:

Lowest Nibble = Lo Local Oscillator Frequency Table Entry Number

Highest Nibble = Hi Local Oscillator Frequency Table Entry Number

Note: see table 2 on page 8 of the “Eutelsat DisEqC slave microcontroller version 1.0”.

PARAM OPTION BYTE

Output Mode and 22 kHz Tone Use (Hi/Lo or SB/SA)

Bit 7:8 = Not used.

Bit 6 = *Decoded Mode With Only Two Lines* (the lowest line of a selection group is kept low)

0: Decoded mode with only two lines not selected

1: Decoded mode with only two lines selected

Bit 5 = *Complementary Mode Selection*

0: Complementary Mode not selected

1: Complementary Mode selected

Bit 4:1 = *Decoded Mode Number*

0: Decoded Mode not selected

1 to 8 : Decoded Mode Number (refer to table 5a on page 11 of the “Eutelsat DisEqC slave microcontroller version 1.0”).

Bit 0 = *22 kHz Tone Use*

0: 22 kHz tone use for Hi/Lo switching in backwards compatible mode

1: 22 kHz tone use for SB/SA switching in backwards compatible mode

Note: if neither a decoded mode nor a complementary output mode is selected, the output mode is the single polarity output mode (refer to Table 3, “Single polarity output mode,” on page 4).

ST7LNB0 DiSEqC™ “slave” MICROCONTROLLER OPTION LIST
 (Last update: December 2004)

Customer
 Address
 Contact
 Phone No

- Family address (tick one box)

Normal LNB (11h)	
Normal Switcher (15h)	

- Backwards Compatible 22 kHz tone usage (tick one box)

Hi/Lo switching	
SB/SA switching	

- Local oscillator frequencies table entry number

Hi L.O table entry number	
Lo L.O table entry number	

- Switching output type: (tick or fill one box)

Single polarity output	
Decoded mode output (indicate the mode number)	
Complementary output	

Comments:

Notes

Signature
 Date

Please download the latest version of this option list from:
<http://www.st.com/mcu> > downloads > ST7 microcontrollers > Option list

9 REVISION HISTORY

Date	Revision	Main changes
September-04	2.0	First release on st.com
December-04	3.0	Changed note 4 and added "optional" in Figure 3 "ST7LNB0 typical application circuit" on page 3 Added default values in Table 5, "ST7LNB0 EEPROM Parameters," on page 7

Notes:

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